FIGURE 1

Starting Substrate: 100 mm-diameter. 400 um-thick (100) Si wafer
Deposition of silicon nitride followed by 4 um -thick polysilicon
Patterning of polysilicon using by photolithography and plasma etching
Thermal oxidation to grow sacrificial SiO ₂ : 10-100 nm
Patterning of oxide (not shown) followed by deposition of 4 um -thick polysilicon
Removal of excess polysilicon using chemical mechanical polishing (CMP)
Let 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1
☐ Si Si ₃ N ₄ ■ Polysilicon ☐ SiO ₂

FIGURE 2

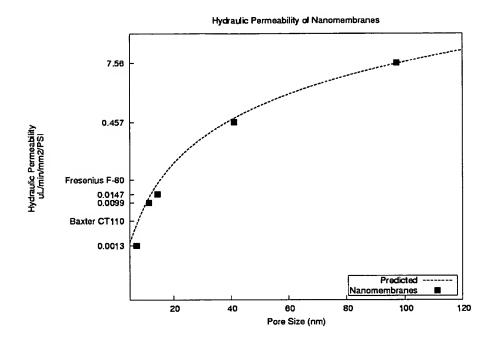
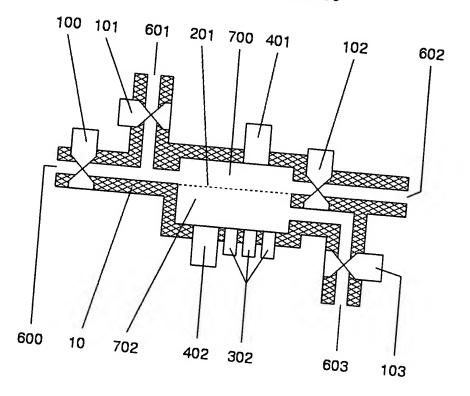


FIGURE 3



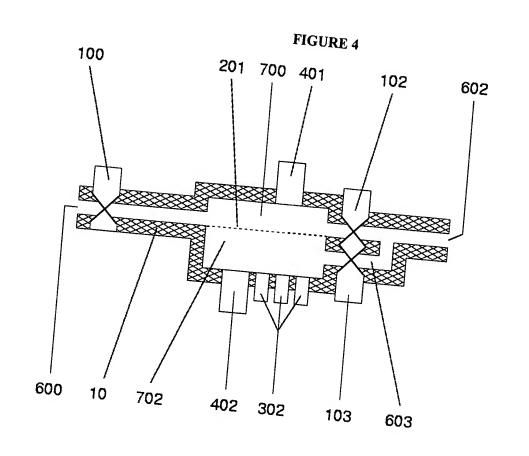


FIGURE 5

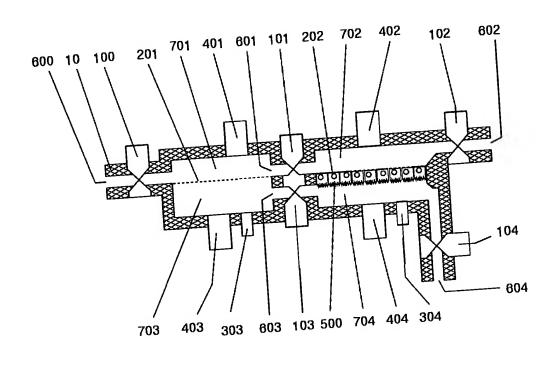


Figure 6

